



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



SiBar Thyristor Surge Protectors TVAxNSA-L Series

SiBar thyristor surge protection devices help protect sensitive telecommunication equipment from the hazards caused by lightning, power contact, and power induction. These devices have a high electrical surge capability to help protect against transient faults and a high off-state impedance, rendering them virtually transparent during normal system operation.

SiBar thyristor surge protectors assist designers to meet telecommunication and computer telephony equipment requirements and industry specifications.



Benefits:

- Helps provide protection for sensitive telecom electronic equipment
- Low leakage current
- Low power dissipation
- Fast, reliable operation
- No wear-out mechanisms
- Assists designers to meet worldwide telecom standards
- Helps reduce warranty and service costs
- Easy installation
- Helps improve power efficiency of equipment

Features:

- RoHS compliant
- Bidirectional crowbar transient voltage protection
- Voltage range: 170V – 275V with improved V_{drm}/V_{bo} range
- High off-state impedance
- Low on-state voltage
- High surge capability
- Short-circuit failure mode
- Surface-mount technology
- DO-214AC SMA package
- 10 x 1000 μ s 50A surge rating
- Helps equipment comply with TIA-968, Telcordia GR-1089, IEC61000-4-5, ITU K.20/21/45

Applications:

- Modems
- Fax machines
- Phones, answering machines
- PBX systems
- Set top boxes
- POS systems
- Analog and digital linecards (xDSL, T1/E1...)
- Other customer premise and central office network equipment requiring protection

SiBar Thyristor Surge Protectors TVAxNSA-L Series

Table SB1 - Electrical Characteristics

Part Number	V _{DM} Max. (V)	V _{BO} Max. (V)	I _H Min. (mA)	V _T Max. (V)	C1 (Typ) 50V _{DC} Bias	C2 (Typ) 2V _{DC} Bias	Off-State Current V _{D2} =V _{DM} (μA)
TVA170NSA-L	170	220	150	4	20	39	5
TVA220NSA-L	220	300	150	4	17	33	5
TVA275NSA-L	275	350	150	4	16	31	5

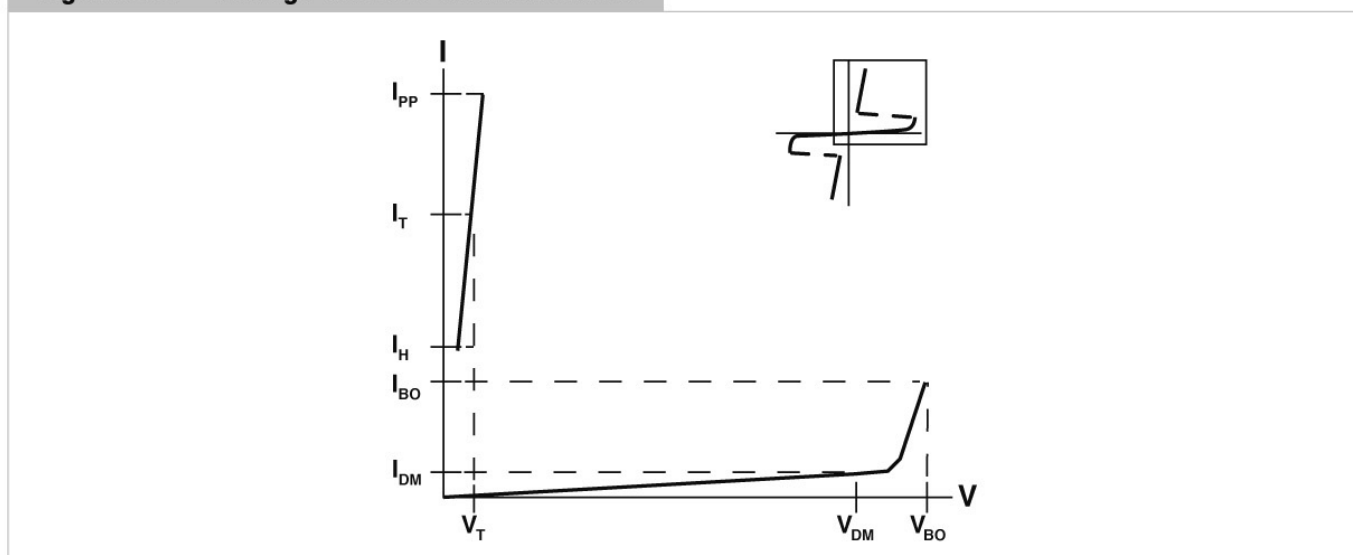
Notes: All electrical characteristics are measured at 25°C.
V_{DM} measured per UL497B pulse requirements: at max. off-state leakage current (IDM) = 5 μA.
V_{BO} measured at 100V/μs.
C1 measured at 1 MHz with a 50 V_{DC} bias.
C2 measured at 1MHz with a 2V_{DC} bias.

Table SB2 – Surge Current Rating

Part Number	TIA-968			Telcordia GR-1089*		IEC61000-4-5	ITU K.20/21/45*			
	Type A	Type B		I _{pp} (A)	I _{pp} (A)	I _{pp} (A)	I _{pp} (A)	I _{TSM} Min. (A)	di/dt (A/μs)	dV/dt (V/μs)
	I _{pp} (A) 5 x 320 μs	I _{pp} (A) 10 x 560 μs	I _{pp} (A) 10 x 160 μs	10 x 1000 μs	2 x 10 μs	8 x 20 μs	5 x 310 μs (VOC: 10 x 700μs)			
TVAxNSA-L	90	70	100	50	150	150	90	22	500	2000

Notes: *Lightning current wave forms for applicable industry specification.
I_{TSM}, peak on-state surge current is measured at 60 Hz, one cycle.
di/dt: critical rate-of-rise of on-state current (pulsed power amplifier Vmax = 600V; C = 30μF).
dV/dt: critical rate-of-rise of off-state voltage (linear wave form, V₀ = rated V_{BO}, T_i = 25°C

Figure SB1 - Voltage-Current Characteristics



The voltage current (V-I) is useful in depicting the electrical characteristics of the SiBar thyristor surge protectors in relation to each other.

SiBar Thyristor Surge Protectors TVAxNSA-L Series

Figure SB2 - Dimension Figure

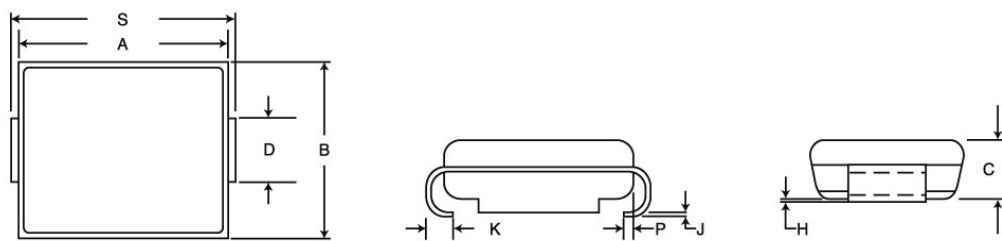


Table SB3 – Dimensions in Millimeters

Dimension	A		B		C		D	
	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
TVAxNSA-L	4.06 (0.160)	4.57 (0.180)	2.25 (0.089)	2.92 (0.115)	1.90 (0.075)	2.41 (0.095)	1.25 (0.049)	1.65 (0.065)

Dimension	H		J		K		P	S	
	Min.	Max.	Min.	Max.	Min.	Max.	Ref	Min	Max.
TVAxNSA-L	0.051 (0.002)	0.200 (0.008)	0.150 (0.006)	0.41 (0.016)	0.76 (0.030)	1.52 (0.060)	0.051 (0.0020)	4.80 (0.189)	5.59 (0.220)

Notes: *D dimension is measured within dimension P.
TVA series devices use industry standard SMA package type.
All devices are bidirectional and may be oriented in either direction for installation

Table SB4 – Physical Characteristics and Environmental Specifications

Lead material	Matte tin finish (-L devices)
Encapsulating material	Epoxy, meets UL94V-0 requirements
Solderability	per MIL-STD-750, Method 2026
Solder heat withstand	per MIL-STD-750, Method 2031
Solvent resistance	per MIL-STD-750, Method 1022
Mechanical shock	per MIL-STD-750, Method 2016
Vibration	per MIL-STD-750, Method 2056
Storage temperature (°C)	-55 to 150
Operating temperature (°C)	-40 to 125
Junction temperature (°C)	175
Maximum Lead Temperature for Soldering Purpose; for 10s (°C)	260

Table SB5 – Reliability Tests

Test	Conditions	Duration
High temperature, reverse bias	+100°C, 50VDC bias	1000 hours
High humidity, high temperature, reverse bias	85% RH, +85°C, 50VDC bias	1000 hours
High temperature storage life	+150°C	1000 hours
Temperature cycling	-65°C to +150°C, 15 minute dwell	1000 cycles
Autoclave	100% RH, +121°C, 15 PSI	96 hours

Document: SCD 27217

Status: Released

Rev: B Date: DECEMBER 12, 2007

SiBar Thyristor Surge Protectors TVAxNSA-L Series

Figures SB3-SB6 - Typical Electrical Characteristics vs. Temperature for Sibar Thyristor Surge Protectors

Figure SB3 - Off-state Voltage vs. Temperature

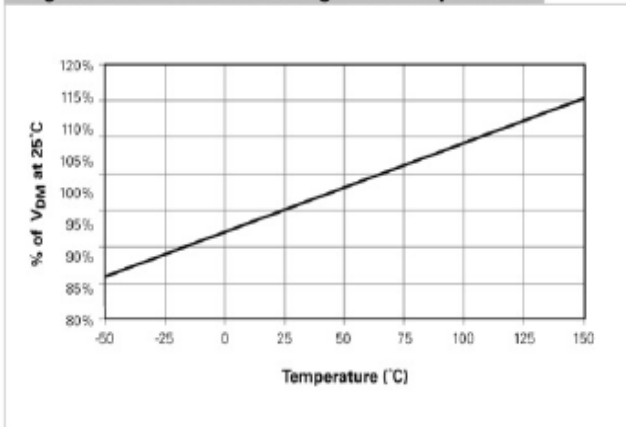


Figure SB4 - Breakover Voltage vs. Temperature

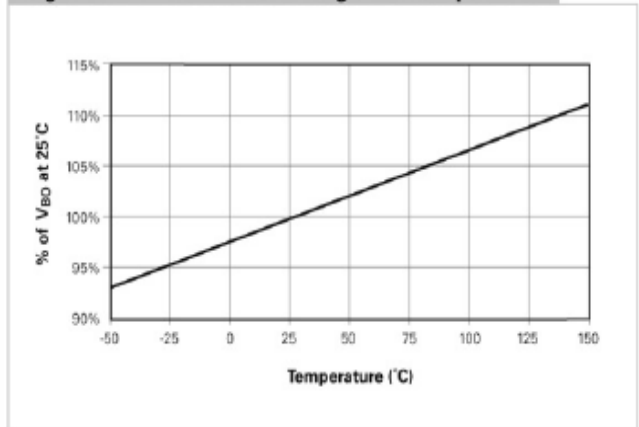


Figure SB5 - Hold Current vs. Temperature

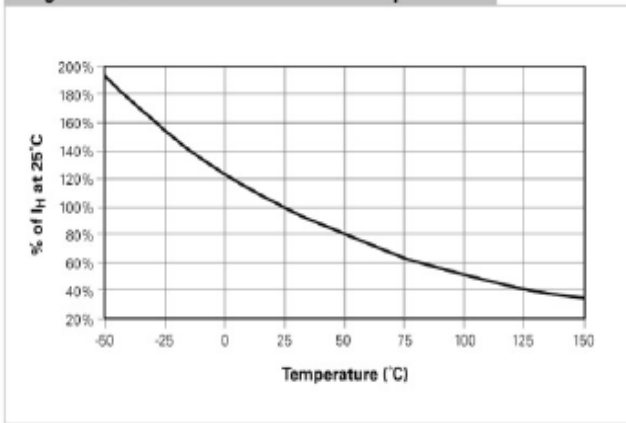
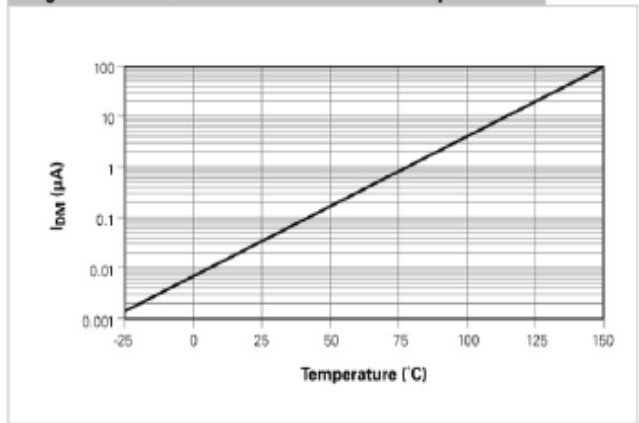


Figure SB6 - Off-state Current vs. Temperature



SiBar Thyristor Surge Protectors TVAXxxNSA-L Series

Figure SB7 - Recommended Pad Layout

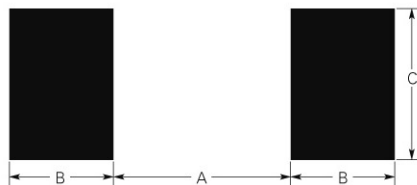


Table SB6 – Packaging and Marking Information

Part Description	Tape and Reel Quantity	Standard Package	Part Marking	Recommended Pad Layout (millimeters/inchs)			Agency Recognition*
				Dimension A (Nom.)	Dimension B (Nom.)	Dimension C (Nom.)	
TVA170NSA-L	5,000	20,000	17NA	2.0 (0.079)	2.0 (0.079)	2.0 (0.079)	**
TVA220NSA-L	5,000	20,000	22NA	2.0 (0.079)	2.0 (0.079)	2.0 (0.079)	**
TVA275NSA-L	5,000	20,000	27NA	2.0 (0.079)	2.0 (0.079)	2.0 (0.079)	**

* UL 497B, File # E179610
**UL Pending